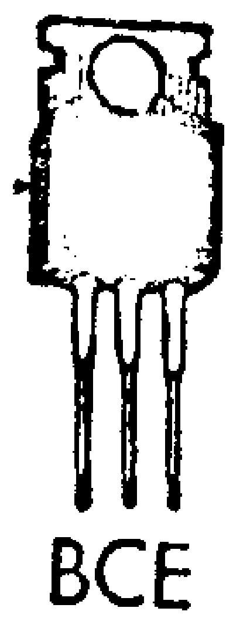
BD 241 · BD 241A · BD 241B

NPN SILICON EPITAXIAL BASE POWER TRANSISTORS

MICRO ELECTRONICS

CASE TO-220B

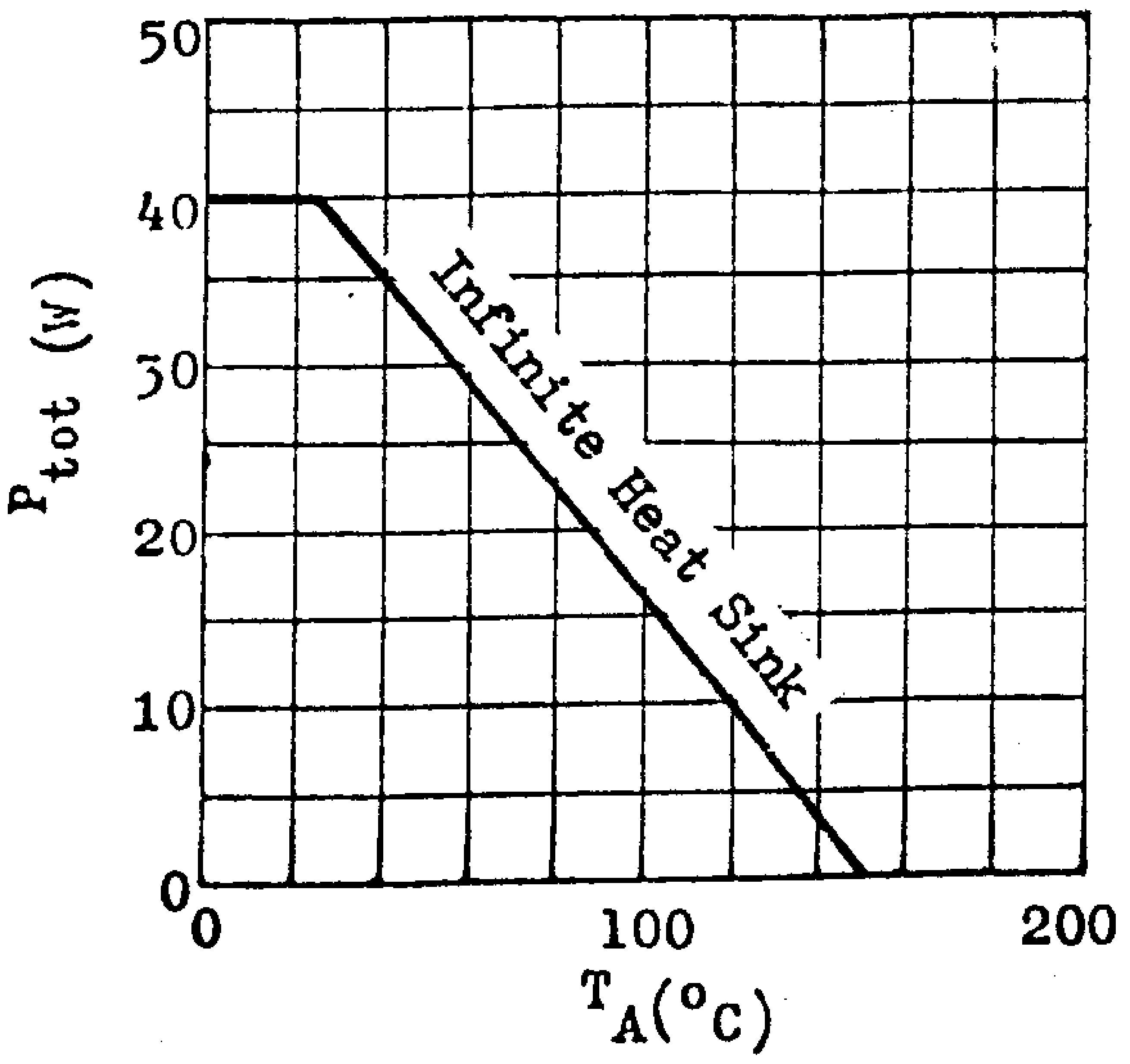


THE BD 241, BD 241A AND BD 241B ARE NPN SILICON EPITAXIAL BASE POWER TRANSISTORS DESIGNED FOR SWITCHING, DRIVER AND OUTPUT STAGES IN AUDIO AMPLIFIERS. THE BD 241, BD 241A AND BD 241B ARE COMPLEMENTARY TO BD 242, BD 242A AND BD 242B RESPECTIVELY.

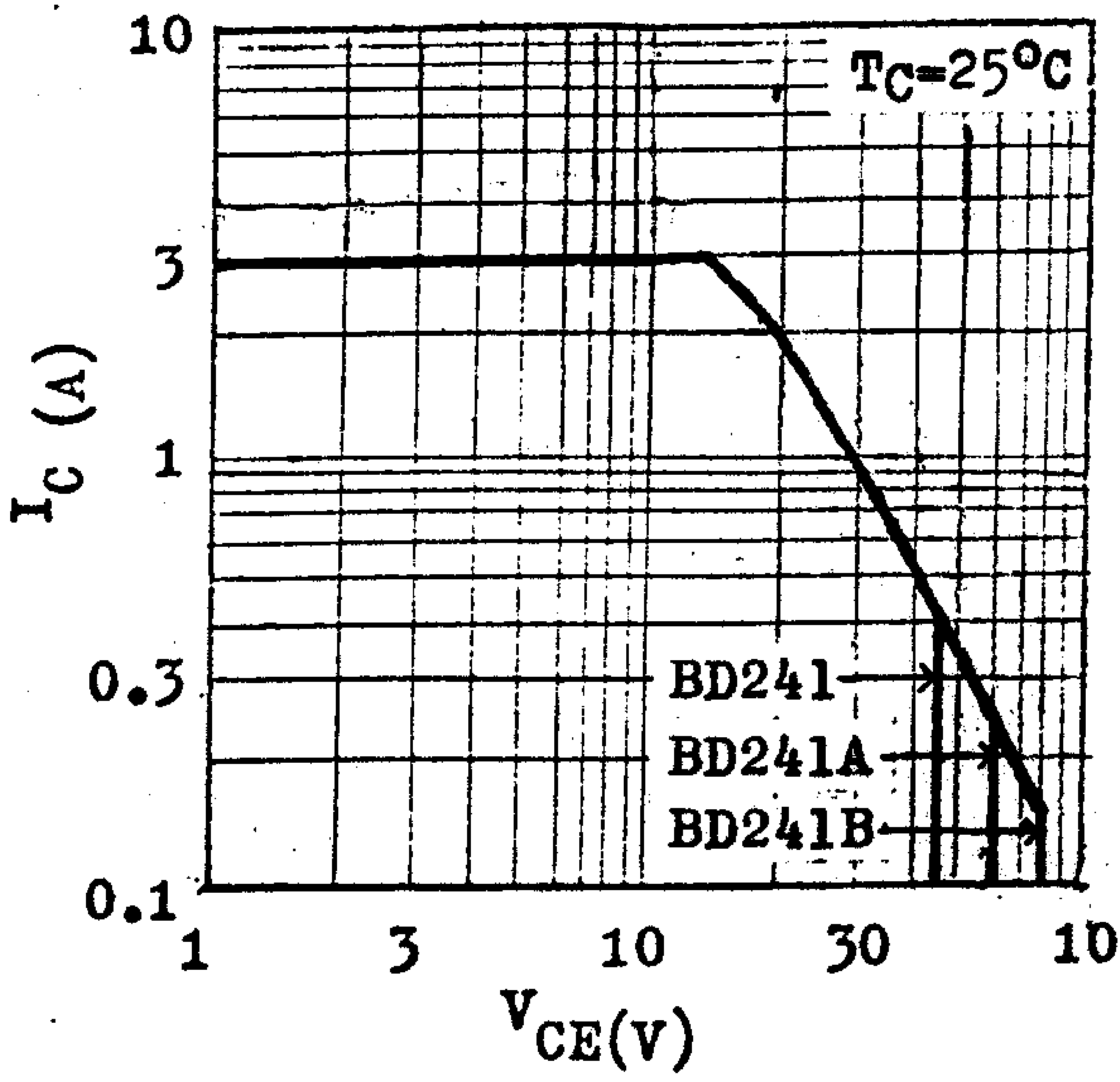
ABSOLUTE MAXIMUM RATINGS		BD241	BD241A	BD241B
Collector-Emitter Voltage (R_{BE}=100Ω)	VCER	55V	70V	90V
Collector-Emitter Voltage (I_B=0)	V_{CEO}	45V	60V	80V
Emitter-Base Voltage	V_{EBO}		5V	
Collector Current	I_C		3A	
Base Current	I_B		1A	
Total Power Dissipation @ $T_C \leqslant 25^oC$	Ptot		40W	
@ $T_A \leqslant 25^oC$			2W	
Junction and Storage Temperature	T_j, T_{stg}		-55 to +150°C	

THERMAL RESISTANCE			
Junction to Case	θ_{jc}	3.12°C/W	max.
Junction to Ambient	θ_{ja}	62.5°C/W	max.

P_{tot} vs T_A



SAFE OPERATING AREA (D.C.)



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